



TAYCHIPST

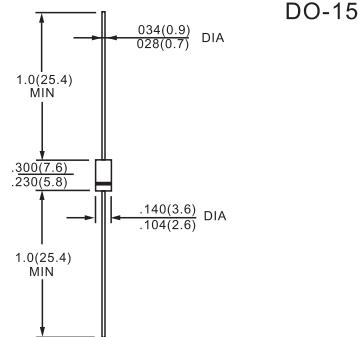
FAST RECOVERY RECTIFIER DIODES

BYT11-600 THRU BYT11-1000

600V-1000V 1.0A

**FEATURES**

- High efficiency
- Low power losses
- Very low switching losses
- Low reverse current
- High surge capability



Dimensions in inches and (millimeters)

**MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS****ABSOLUTE RATINGS** (limiting values)

Symbol	Parameter	Value	Unit
I <sub>FRM</sub>	Repetitive Peak Forward Current	20	A
I <sub>F</sub> (AV)	Average Forward Current *	1	A
I <sub>FSM</sub>	Surge non Repetitive Forward Current	35	A
P <sub>tot</sub>	Power Dissipation *	1.25	W
T <sub>stg</sub> T <sub>j</sub>	Storage and Junction Temperature Range	- 55 to + 150 - 55 to + 150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering during 10s at 4mm from Case	230	°C

Symbol	Parameter	BYT 11-			Unit
		600	800	1000	
V <sub>RRM</sub>	Repetitive Peak Reverse Voltage	600	800	1000	V

**ELECTRICAL CHARACTERISTICS****STATIC CHARACTERISTICS**

Symbol	Test Conditions	Min.	Typ.	Max.	Unit
I <sub>R</sub>	T <sub>j</sub> = 25°C V <sub>R</sub> = V <sub>RRM</sub>			20	µA
V <sub>F</sub>	T <sub>j</sub> = 25°C I <sub>F</sub> = 1A			1.3	V

**RECOVERY CHARACTERISTICS**

Symbol	Test Conditions	Min.	Typ.	Max.	Unit
t <sub>rr</sub>	T <sub>j</sub> = 25°C I <sub>F</sub> = 0.5A I <sub>R</sub> = 1A I <sub>rr</sub> = 0.25A			100	ns



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## RATINGS AND CHARACTERISTIC CURVES

## BYT11-600 THRU BYT11-1000

Figure 1. Maximum average power dissipation versus average forward current.

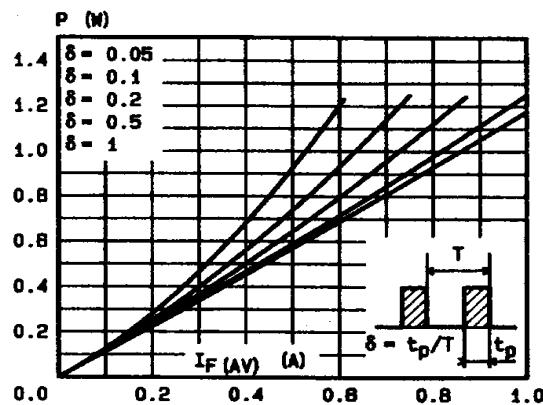


Figure 3. Thermal resistance versus lead length.

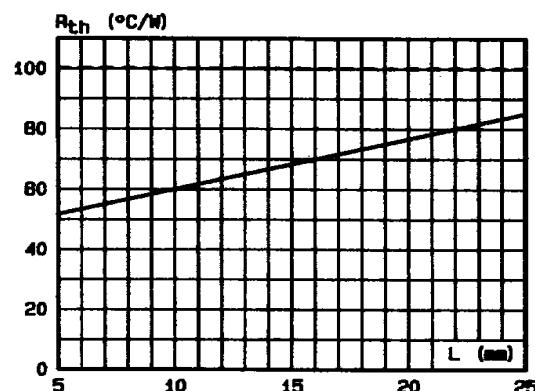


Figure 4. Transient thermal impedance junction-ambient for mounting n°2 versus pulse duration ( $L = 10$  mm).

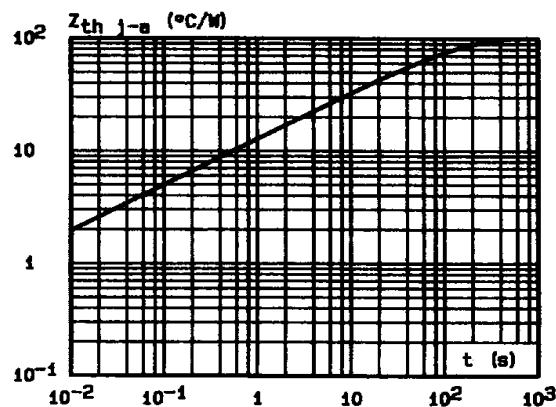


Figure 2. Average forward current versus ambient temperature.

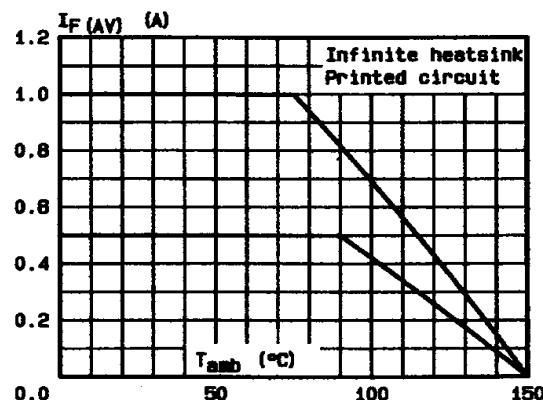


Figure 5. Peak forward current versus peak forward voltage drop (maximum values).

